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Failure Modes in Carbon Nanotube Devices S.L. KONSEK, MSD, LBNL, Berkeley, Caifornia 94720 and Dept. of Physics, UC Berkeley, California, 94720, SHAUL ALONI, Molecular Foundry MSD, LBNL, Berkeley, Caifornia 94720 and Dept. of Physics, UC Berkeley, California, 94720, B.C. REGAN, ALEX ZETTL, MSD, LBNL, Berkeley, Caifornia 94720 and Dept. of Physics, UC Berkeley, California, 94720 — We study the electrical breakdown of multiwall carbon nanotube transistor devices. Electrical transport measurements are preformed in a transmission electron microscope, allowing real-time nanometer scale imaging of device breakdown. Failure modes are correlated to changes in nanotube device behavior.

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